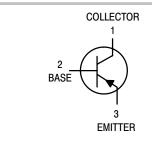
# **Amplifier Transistors**

# **PNP Silicon**



# ON Semiconductor™

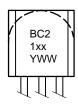
### http://onsemi.com





TO-92 CASE 29 STYLE 17

### **MARKING DIAGRAMS**



BC21xx = Specific Device Code

xx = 2, 2B, or 3 Y = Year WW = Work Week

### **ORDERING INFORMATION**

Device	Package	Shipping
BC212	TO-92	5000 Units/Box
BC212B	TO-92	5000 Units/Box
BC212BRL1	TO-92	2000/Tape & Reel
BC212BZL1	TO-92	2000/Ammo Pack
BC213	TO-92	5000 Units/Box

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC212 BC213	VCEO	-50 -30	Vdc
Collector-Base Voltage BC212 BC213	VCBO	-60 -45	Vdc
Emitter-Base Voltage	VEBO	-5.0	Vdc
Collector Current – Continuous	IC	-100	mAdc
Total Device Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	PD	350 2.8	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	125	°C/W

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = -2.0 mAdc, I <sub>B</sub> = 0)	BC212 BC213	V(BR)CEO	-50 -30	- -	_ _	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0)	BC212 BC213	V(BR)CBO	-60 -45	- -	- -	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)	BC212 BC213	V(BR)EBO	-5 -5	- -	- -	Vdc
Collector–Emitter Leakage Current (V <sub>CB</sub> = -30 V)	BC212 BC213	СВО	- -	- -	-15 -15	nAdc
Emitter–Base Leakage Current (V <sub>EB</sub> = -4.0 V, I <sub>C</sub> = 0)	BC212 BC213	IEBO	- -	- -	-15 -15	nAdc
ON CHARACTERISTICS						
DC Current Gain ( $I_C = -10 \mu Adc$ , $V_{CE} = -5.0 \text{ Vdc}$ )	BC212 BC213	hFE	40 40	- -	_ _	-
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC212 BC213		60 80	- -	_ _	
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$ (Note 1.)	BC212 BC213		- -	120 140	_ _	
Collector–Emitter Saturation Voltage ( $I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ( $I_C = -100$ mAdc, $I_B = -5.0$ mAdc) (Note 1.)		VCE(sat)	- -	-0.10 -0.25	_ 	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = $-100$ mAdc, I <sub>B</sub> = $-5.0$ mAdc)		V <sub>BE(sat)</sub>	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc)		V <sub>BE</sub> (on)	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS		•		•	•	
Current–Gain – Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	BC212 BC213	fT	- -	280 360	_ _	MHz
Common–Base Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	-	-	6.0	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, f = $200$ Hz)	BC212, BC213	NF	-	_	10	dB
Small–Signal Current Gain (IC = -2.0 mAdc, VCE = -5.0 Vdc, f = 1.0 kHz)	BC212 BC213 BC212B	h <sub>fe</sub>	60 80 200	- - -	- - 400	_

Pulse Test: Tp 300 s, Duty Cycle 2.0%.

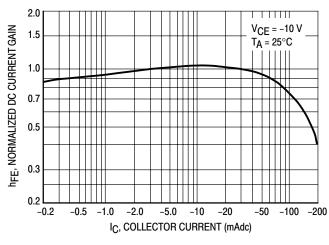


Figure 1. Normalized DC Current Gain

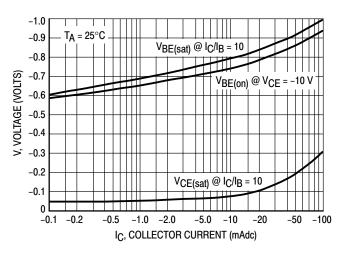


Figure 2. "Saturation" and "On" Voltages

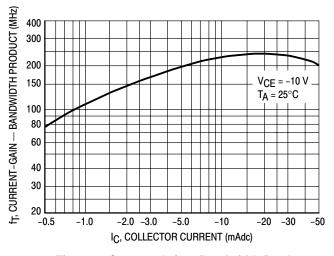


Figure 3. Current-Gain - Bandwidth Product

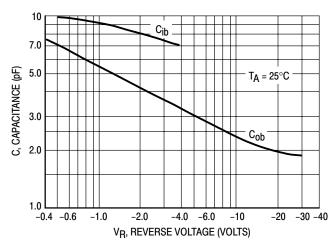


Figure 4. Capacitances

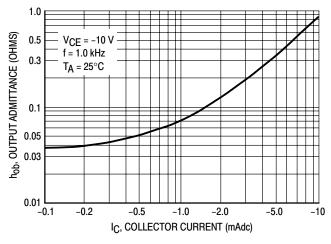


Figure 5. Output Admittance

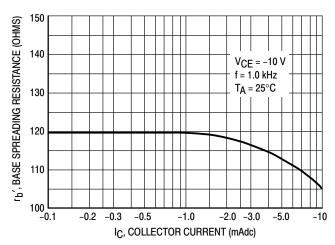
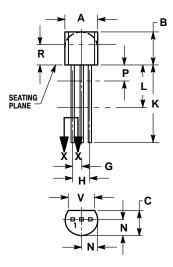


Figure 6. Base Spreading Resistance

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- 114-30M, 1902.
  CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
  LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

#### STYLE 17:

- PIN 1. COLLECTOR
  - BASE
  - 2. 3. EMITTER

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